

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,835,578 B1
DATED : December 28, 2004
INVENTOR(S) : Li-Te S. Lin et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

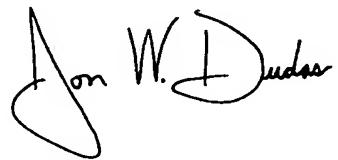
Column 1,

Line 5, insert -- FIELD OF THE INVENTION

The present invention relates generally to semiconductor fabrication and more specifically to test structures used to determine stress migration. --

Signed and Sealed this

Twelfth Day of July, 2005



JON W. DUDAS
Director of the United States Patent and Trademark Office